

VS-1EQH01HM3, VS-1EQH02HM3

Vishay Semiconductors

AUTOMOTIVE

COMPLIANT HALOGEN

FREE

Ultrafast Rectifier, 1 A FRED Pt®



MicroSMP (DO-219AD)

Anode O Cathode

LINKS TO ADDITIONAL RESOURCES

Operating junction and storage temperatures



PRIMARY CHARACTERISTICS				
I _{F(AV)}	1 A			
V_R	100 V, 200 V			
V _F at I _F	0.72 V			
t _{rr} (typ.)	33 ns			
I _{FSM}	30 A			
T _J max.	175 °C			
Package	MicroSMP (DO-219AD)			
Circuit configuration	Single			

FEATURES

- Very low profile typical height of 0.65 mm
- · Ideal for automated placement
- · Low forward voltage drop, low power losses
- · Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- For PFC, CRM snubber operation
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

For use in high frequency, freewheeling, DC/DC converters, PFC, and in snubber industrial and automotive applications.

MECHANICAL DATA

Case: MicroSMP (DO-219AD)

Molding compound meets UL 94 V-0 flammability rating **Terminals:** matte tin plated leads, solderable per

-55 to +175

°C

J-STD-002, meets JESD 201 class 2 whisker test

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS PARAMETER SYMBOL TEST CONDITIONS VALUES UNITS VS-1EQH01HM3 100 Peak repetitive reverse voltage V_{RRM} VS-1EQH02HM3 200 Average rectified forward current $T_M = 159 \, ^{\circ}C$ 1 I_{F(AV)} Α $T_J = 25$ °C, 10 ms sine pulse 30 Non-repetitive peak surge current I_{FSM}

T_J, T_{Stg}

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	VS-1EQH01HM3	V _{BR} , V _R I _R = 100 μA	L = 100 uA	100	-	-	V
	VS-1EQH02HM3		Ι _R = 100 μΑ	200			
Carriered wellte are		V	I _F = 1 A	-	0.88	0.97	- V
Forward voltage		V_{F}	I _F = 1 A, T _J = 150 °C	-	0.72	0.75	
Deverse leekees eurment			V _R = V _R rated	-	-	1	
Reverse leakage current		I _R	T _J = 150 °C, V _R = V _R rated	-	-	25	μΑ
Junction capacitance		C _T	V _R = 200 V	-	6	-	pF

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A, } dI_F/dt =$	0 A, $dI_F/dt = 50 \text{ A/}\mu\text{s}$, $V_R = 30 \text{ V}$		33	-	
Payarea raggivery time		I _F = 0.5 A, I _R = 1 A, I _{rr} = 0.25 A		-	-	23	
Reverse recovery time	t _{rr}	T _J = 25 °C	I _F = 1 A dI _F /dt = 200 A/μs V _R = 100 V	-	13	-	ns -
		T _J = 125 °C		-	18	-	
Peak recovery current		T _J = 25 °C		-	1.8	-	А
	I _{RRM}	T _J = 125 °C		-	2.7	-	
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	11	-	nC
		T _J = 125 °C		-	23	-	110

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range		T _J , T _{Stg}		-55	-	175	°C
Thermal resistance, junction to mount		R _{thJM} ⁽¹⁾		-	16	20	
Thermal resistance, junction to ambient		R _{thJA}	Device mounted on FR4 PCB, 2 oz. standard footprint	-	160	-	°C/W
Approximate weight					0.006		g
Marking device	VS-1EQH01HM3		Case style MicroSMP (DO-219AD)	1H1			
Marking device	VS-1EQH02HM3		Case style MicrosiMF (DO-219AD)	1H2			

Note

⁽¹⁾ Thermal resistance junction to mount follows JEDEC® 51-14 transient dual interface test method (TDIM)

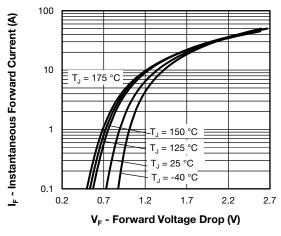


Fig. 1 - Typical Forward Voltage Drop Characteristics

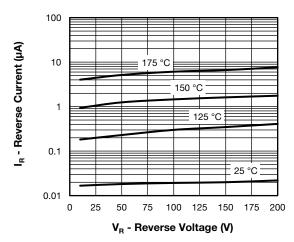


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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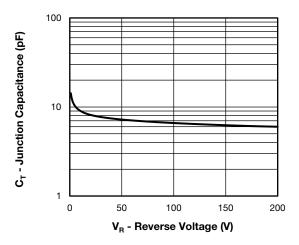


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

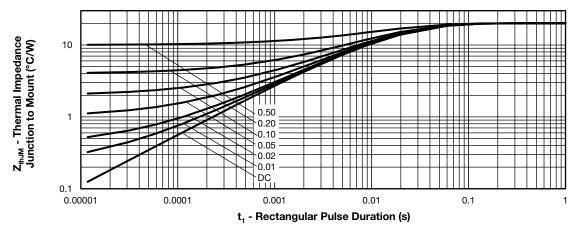


Fig. 4 - Maximum Transient Thermal Impedance, Junction to Mount

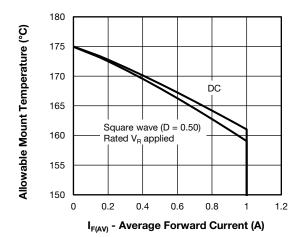


Fig. 5 - Maximum Allowable Mount Temperature vs. Average Forward Current

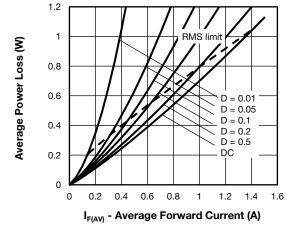


Fig. 6 - Forward Power Loss Characteristics

Note

Formula used: $T_M = T_J - (Pd + Pd_{REV}) \times R_{thJM}$; $Pd = forward power loss = I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 5); $Pd_{REV} = inverse power loss = V_{R1} \times I_R$ (1 - D); I_R at $V_{R1} = rated V_R$

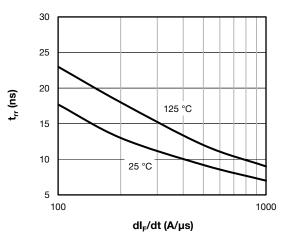


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

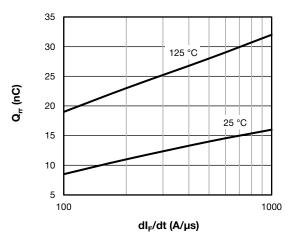
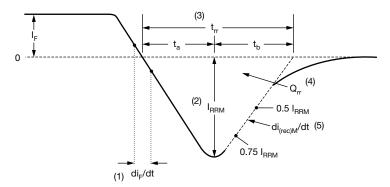


Fig. 8 - Typical Stored Charge vs. dl_F/dt



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm l_{r}$ to point where a line passing through 0.75 $\rm l_{RRM}$ and 0.50 $\rm l_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

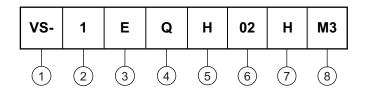
Fig. 9 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (1 = 1 A)

Circuit configuration:

E = single diode

4 - Q = MicroSMP package

5 - Process type,

H = ultrafast recovery

• Voltage code (02 = 200 V)

7 - H = AEC-Q101 qualified

8 - M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)						
PREFERRED P/N PREFERRED PACKAGE CODE MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION						
VS-1EQH01HM3/H	Н	4500	7" diameter plastic tape and reel			
VS-1EQH02HM3/H	Н	4500	7" diameter plastic tape and reel			

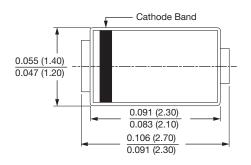
LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?96591</u>				
Part marking information	www.vishay.com/doc?96590			
Packaging information	www.vishay.com/doc?88869			
SPICE model	www.vishay.com/doc?96594			

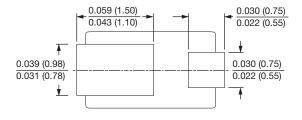


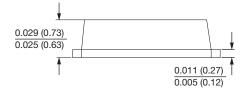
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MicroSMP (DO-219AD), FRED Pt®

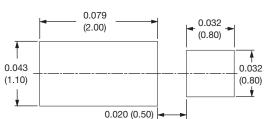
DIMENSIONS in inches (millimeters)







Mounting Pad Layout





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